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I. In the Claims:

Please add the following claims:

14. (Newly Added) A method of forming a wiring film, the method comprising:

providing a substrate;

depositing a Ti layer over said substrate;

depositing an Al-Si-Cu layer on said Ti layer, which forms an Al_3Ti on said

Ti layer; and

pattern etching an Al layer, which forms beneath said Al-Si-Cu layer.

15. (Newly Added) A method as recited in claim 14, wherein said Al-Si-Cu layer is deposited at a temperature of at least 400 °C.

16. (Newly Added) A method as recited in claim 14, wherein said substrate is annealed at a temperature of at least 400 °C.

17. (Newly Added) A method of forming a wiring film, the method comprising:

providing a substrate;

depositing an Al_3Ti layer over said substrate;

depositing an Al layer on said Al_3Ti layer; and